

Developments in low-temperature metal-based packaging

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- Project & Research goals
- Low temperature metal packaging
 - Dry thermocompression
 - Rapid Thermal process
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 - Insertion of thin metal layer
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Research goals

Center for Micro/Nano Scaling Induced Physics (MiNaSIP) in U.C. Berkeley

- Subgroup research with Freescale™ semiconductor

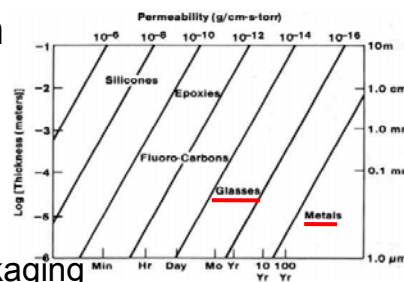
- Flux-less bonding
- Short bonding time & Low bonding temp.
- Sub-100μm width bonding ring
 - Photolithography definable & Electroplating
- Hermetic sealing
 - Low permeability required
- CMOS compatible process



Material selection

• Material Selection Criteria

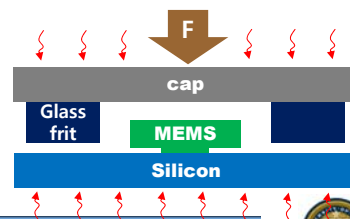
- Temperature
- Deposition & bonding method
- Permeability
- Mechanical properties



*Glass Frit : Popular in MEMS packaging

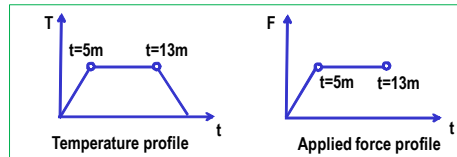
- Deposition : Screen-printing (min.w≈150μm)
- Temperature : 450 °C
- Time :15-30 minutes
- Mechanical : Brittle

→ **Metal bonding**



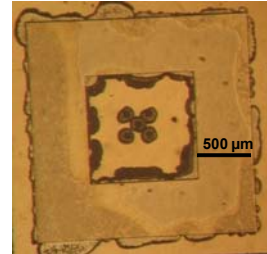
Dry Thermo-Compression (SnCu-Cu)

- $227 > T_{\text{bond}} > 232$

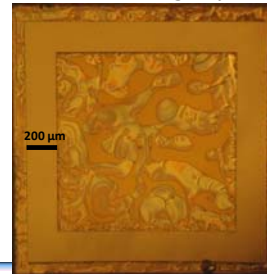


< Flipchip bonding parameters >

- Results:
 - No bond or Solder reflowed
- Low process controllability
 - Non-planar surface issue
 - Surface oxidation may prevent inter-diffusion

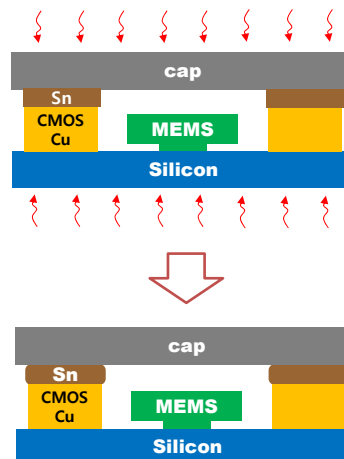


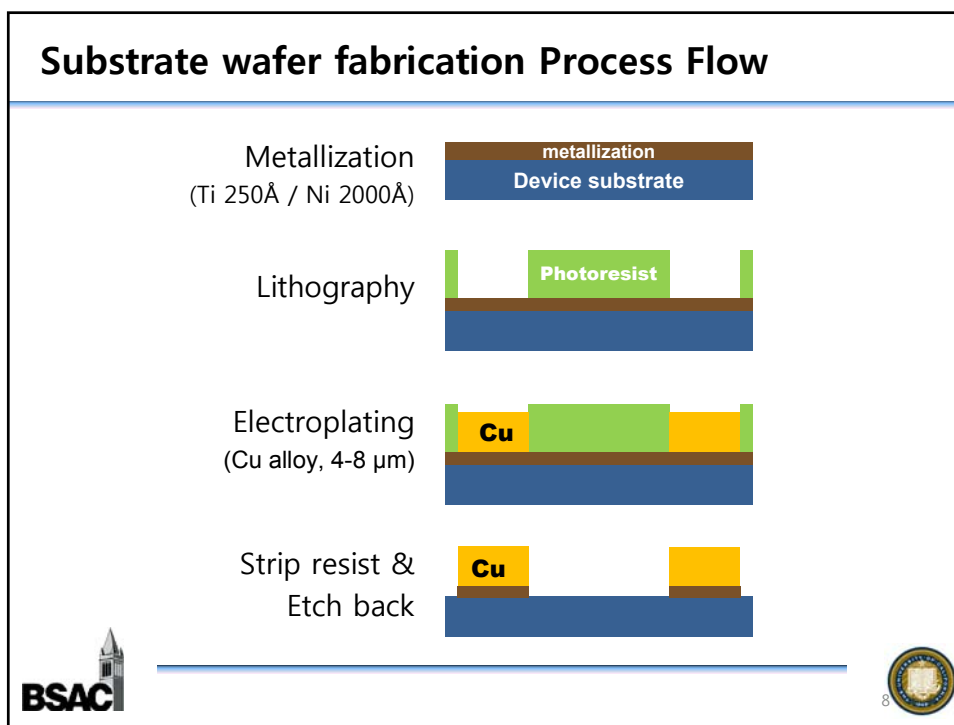
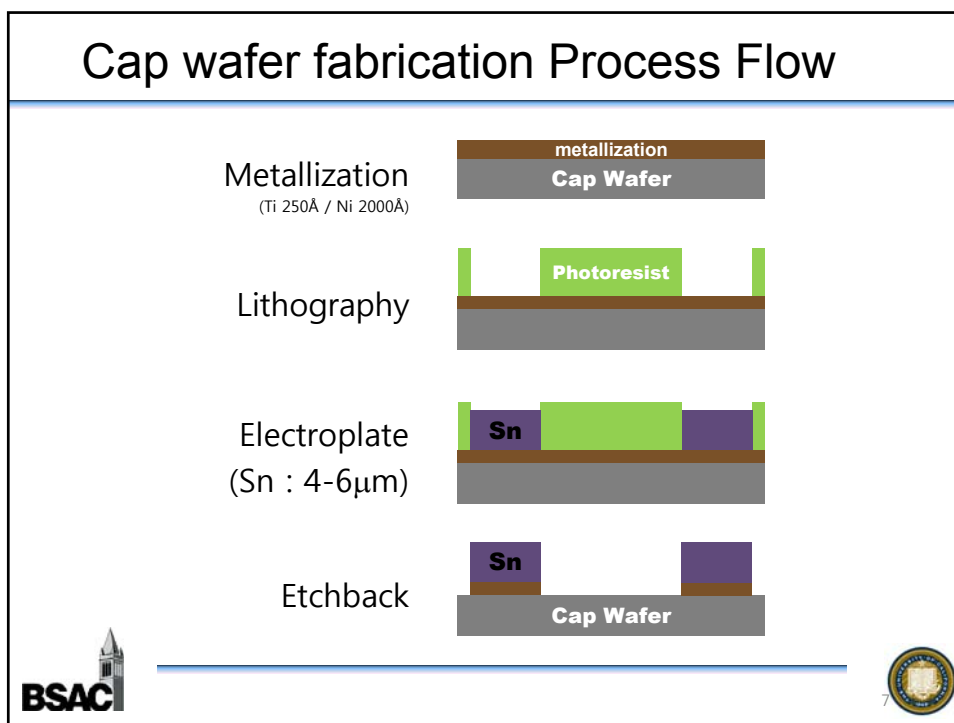
Bond viewed through pyrex cap



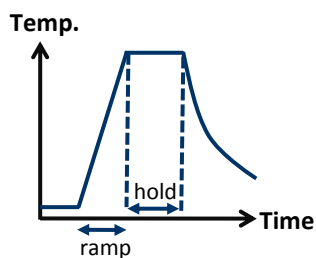
Sn Reflow Bonding via RTP

- RTP (Rapid Thermal Process)
 - Short bonding time with high temperature ramping up speed to prevent solder's squeezing out
- Solder reflow benefits
 - + Less sensitive to surface non-uniformities
 - + Low force

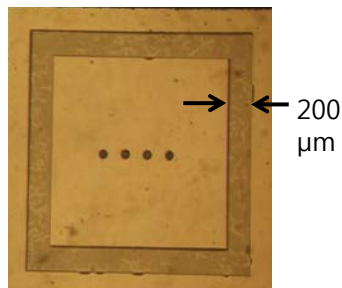




RTP Bonds – Minimal Thermal Budget



$T_{\max} = 250-300\text{ }^{\circ}\text{C}$
ramp = 10 seconds
hold = 10 seconds



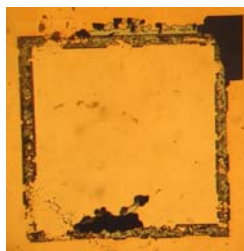
- Thermal budgeting compared to glass frit
 - Time reduction – 10-50X
 - Temperature reduction – 1.5-2X



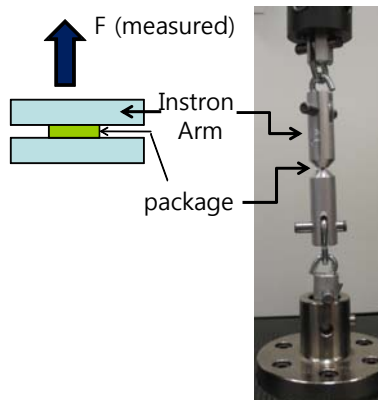
Mechanical strength comparable with glass frit

Material System	Bond Strength (MPa)
Glass frit (thermo-compression)	8.5
Solder reflow (RTP)	7.5

pull-tested bond

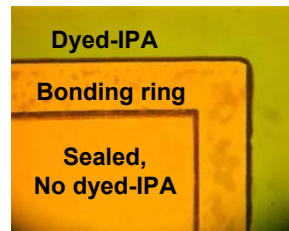
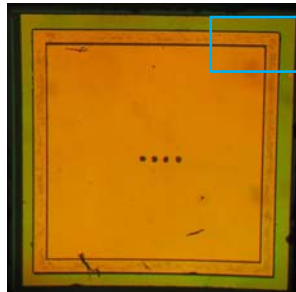


Pull-Test Setup



Leak & Autoclave Test

- Dyed-IPA leak test
 - Gross-leak detection
 - Small surface tension of IPA allows quick permeation through voids



12-hour Autoclave test failed : 125°C & 24psi



Why hermetic test failed??

- *Formation of leakage pass-through due to...*
- Void formation
 - Gas trapping during bonding process
 - Metal oxide on surface prevents reflow of solder
- Non-uniform bonding along the bonding ring
 - Lack of uniform pressure applied during bonding

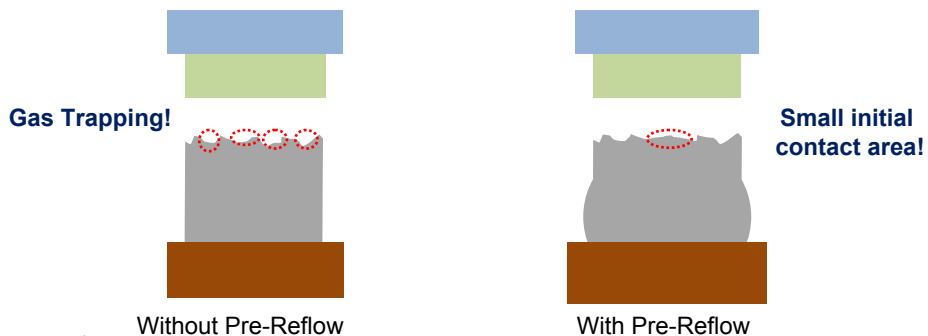
→ **Pre-reflow process approach**



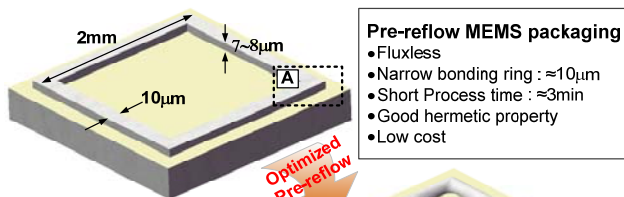
Pre-Reflow process

♦ Purpose of Pre-reflow process

- Break the surface oxide layer and reflow fresh solder
- To minimize gas trapping which causes void formation in bonding area



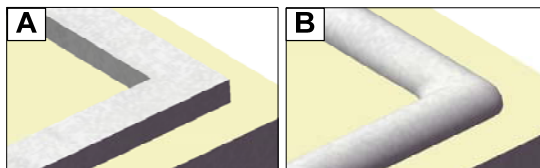
Pre-reflow bonding concept

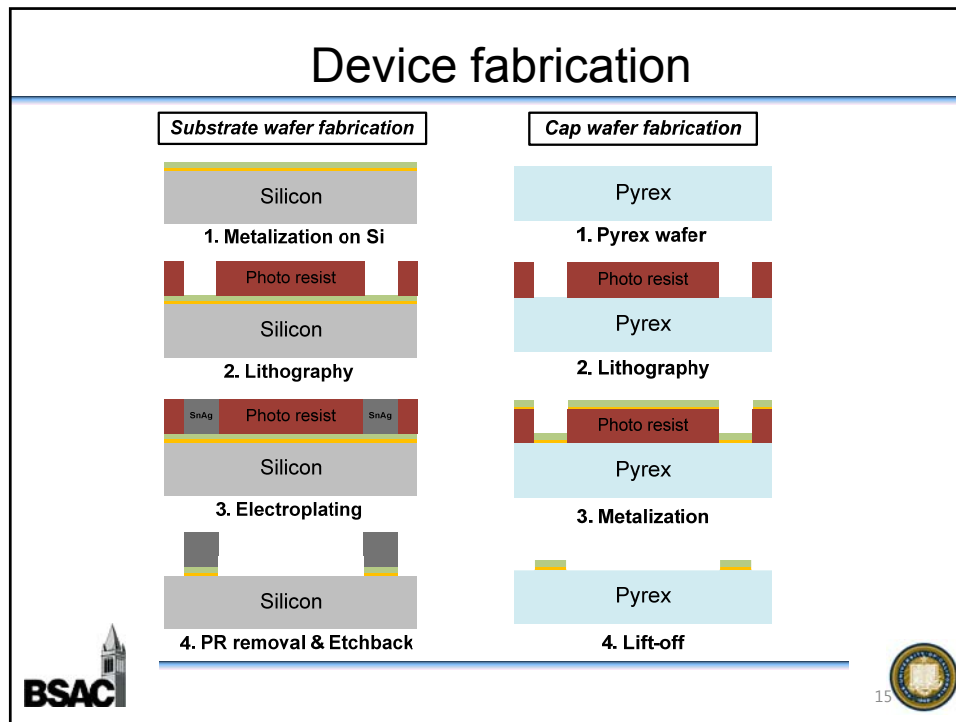


Pre-reflow MEMS packaging

- Fluxless
- Narrow bonding ring : $\approx 10\mu\text{m}$
- Short Process time : $\approx 3\text{min}$
- Good hermetic property
- Low cost

	Pre-reflow	Glass-Frit
Width	$\approx 10\mu\text{m}$	$> 150\mu\text{m}$
Time	$\approx 3\text{min}$	15~30min






Pre-reflow profile optimization


- Process parameters in typical solder ball reflow process
 - Temperature gradient in preheat zone
 - Soak temperature and time when using Flux
 - Temperature gradient from soak to maximum temperature
 - Maximum peak temperature
 - Cooling gradient in cooling zone
 - Total heating time

- Current solder reflow profile is optimized for **solder ball to form sphere shape not for square line form solder**
 - Reflow profile needs to be modified for line shape bonding



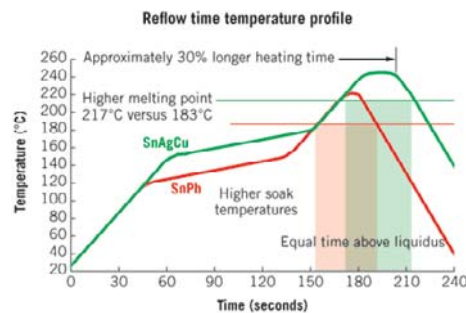
BSAC

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Typical solder ball reflow profile

- **Typical solder ball reflow profile**
 - SnAgCu & SnPb case
 - $\approx 20^{\circ}\text{C} \sim 30^{\circ}\text{C}$ higher peak temperature than melting temperature
 - $\approx 40\text{sec}$ of time above melting temperature
 - Total of 3~5min of process



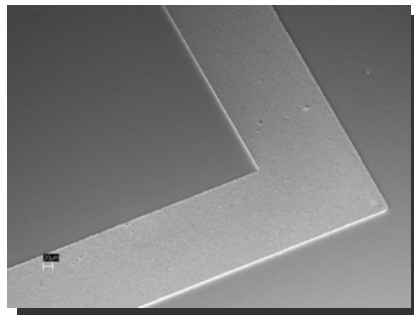
• Denis Barbini et al. "Process Considerations for optimizing a reflow profile", SMT/July 2005, www.smtmag.com



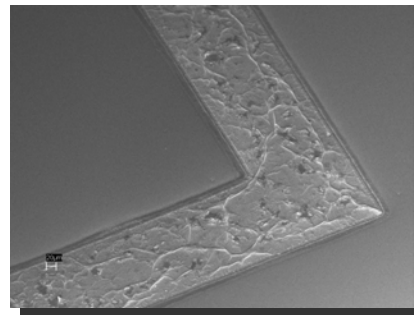
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SnAg solder with Pre-reflow test

- Electroplated Sn(96.5)Ag(3.5) eutectic solder
- Bonding ring dimension: Width $\approx 200\mu\text{m}$, Height $\approx 6\mu\text{m}$



Before reflow



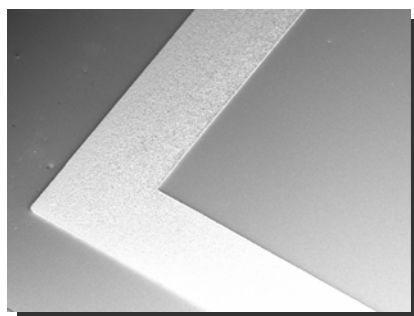
After reflow



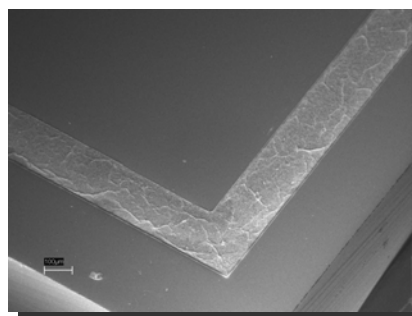
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SnCu eutectic solder with Pre-reflow test

- Electroplated Sn(99.3)Cu(0.7) eutectic solder
- Bonding ring dimension: Width $\approx 200\mu\text{m}$, Height $\approx 5\mu\text{m}$



Before reflow

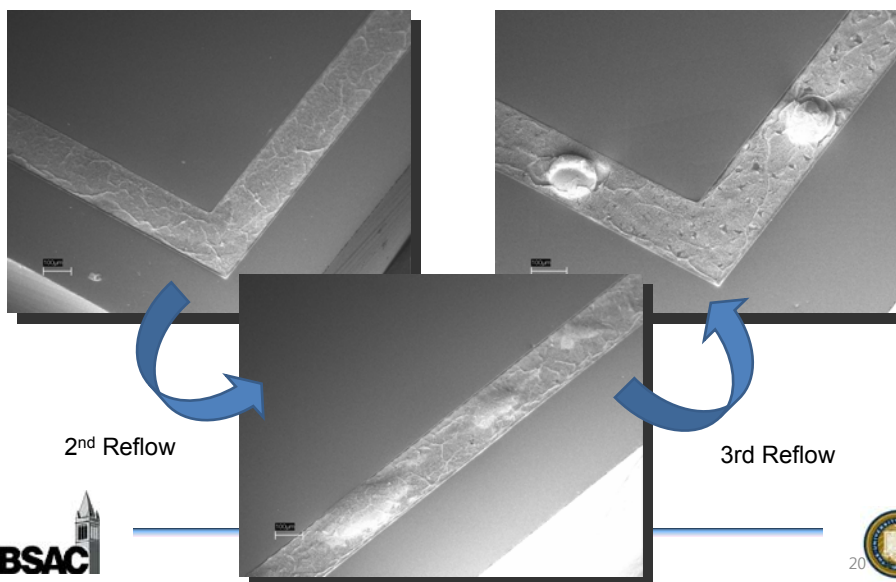


After reflow



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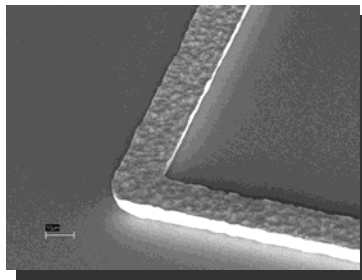
SnCu solder with multiple reflow processes



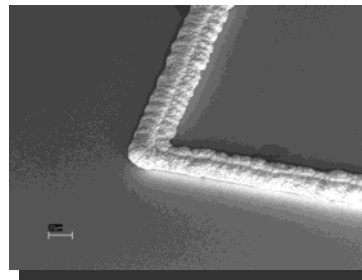
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Low Width to Height ratio bonding ring

- Electroplated 10 μ m and 20 μ m width bonding ring
- Width to Height ratio - 1.5:1~2:1



Electroplated **SnAg**
with 10 μ m width bonding ring



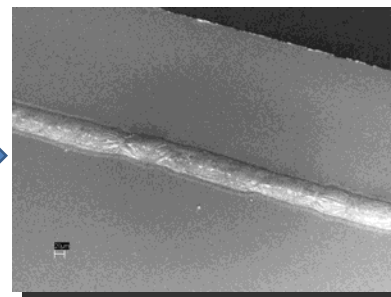
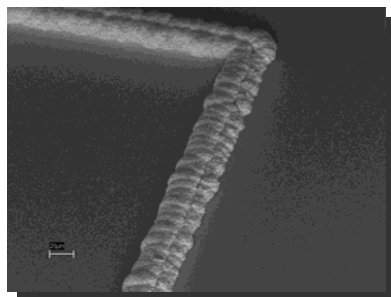
Electroplated **SnCu**
with 20 μ m width bonding ring



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SnCu reflow test results

- Reflow profile modification
- Formed half-cylinder after reflow
- Partially non-uniform clogging surfaces observed



Electroplated SnCu
with 20 μ m bonding ring

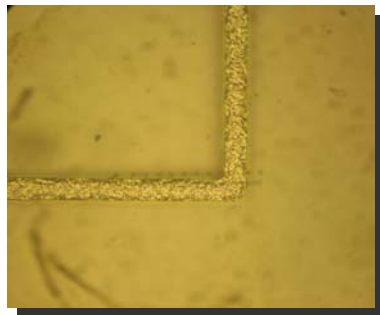
After reflow



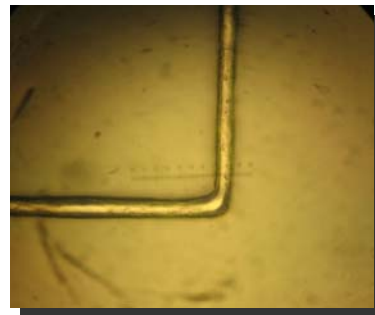
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SnAg 10 μ m width ring pre-reflow results

- Reflow profile optimized in RTP
- Uniform half-cylinder shape achieved
- No clogging or solder gathering was observed



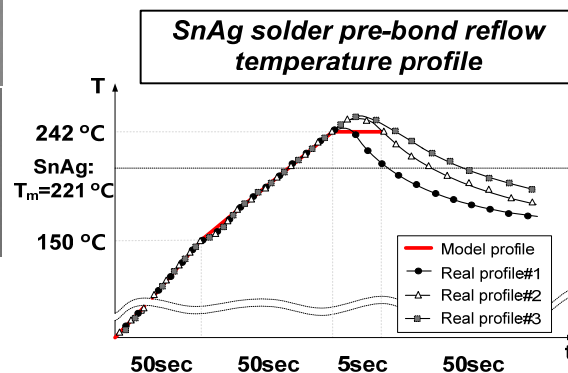
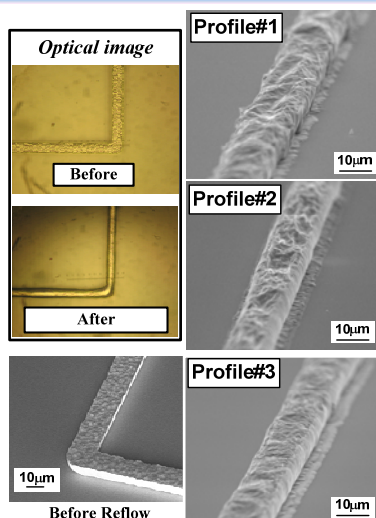
Electroplated SnAg
with 10 μ m width bonding ring

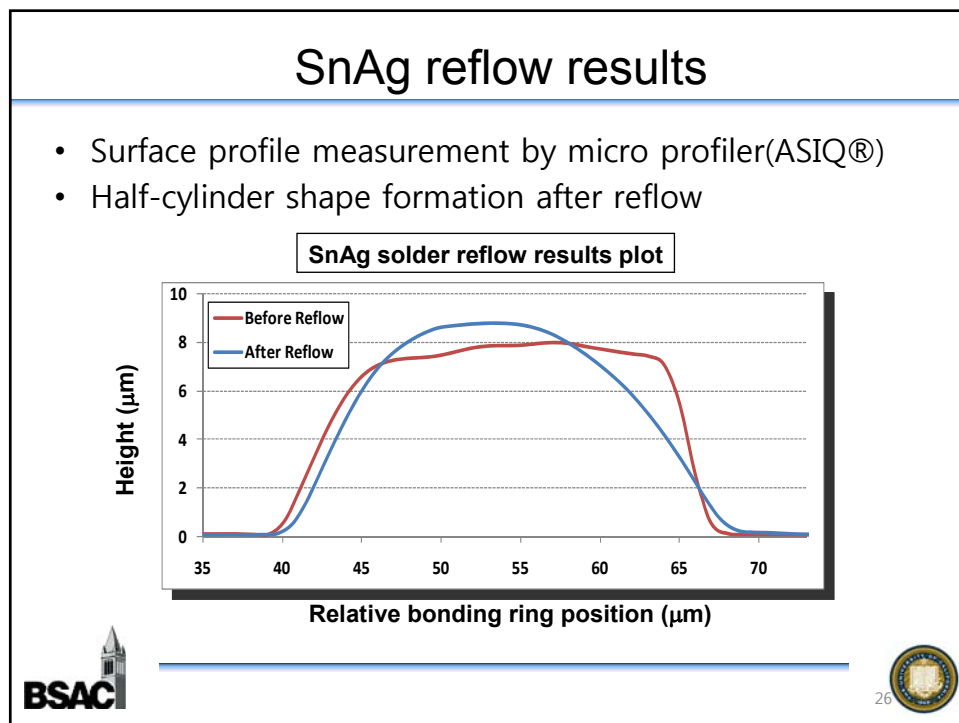
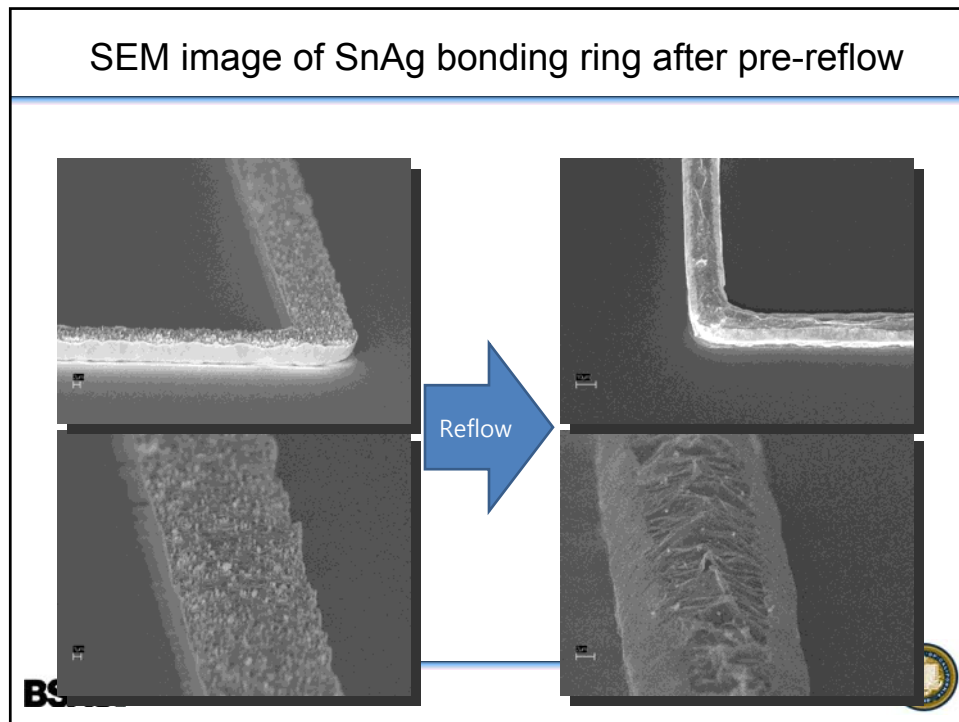


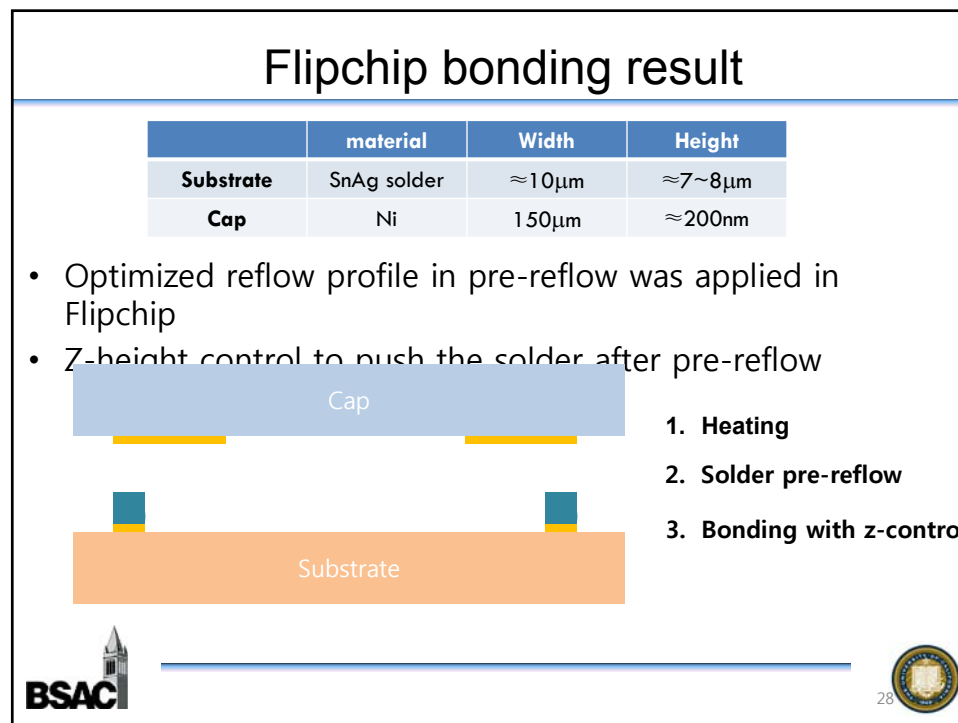
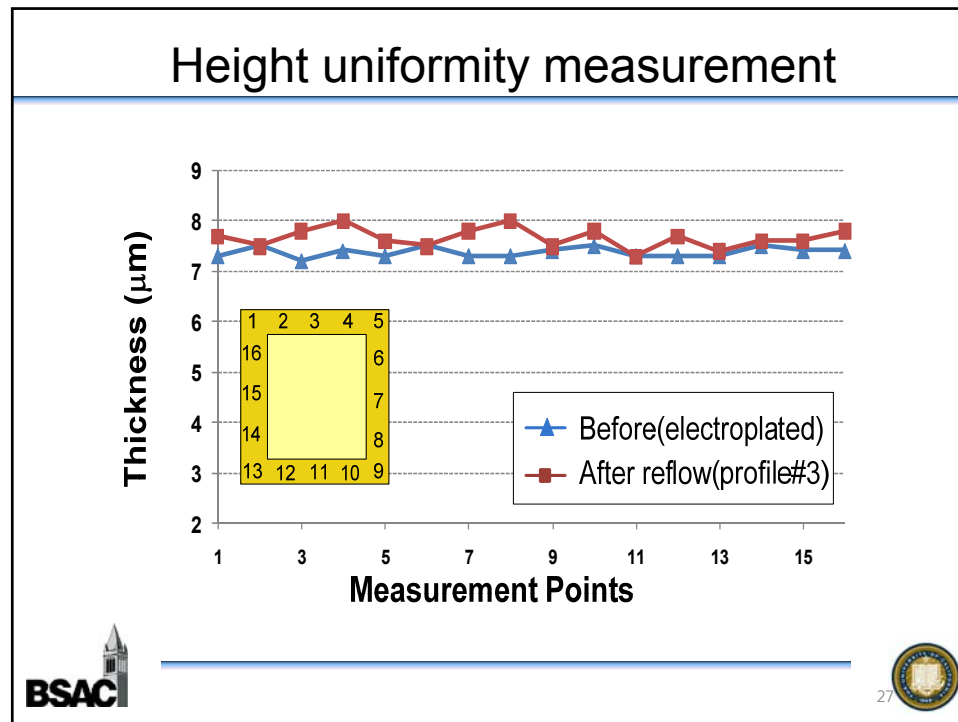
After optimized reflow

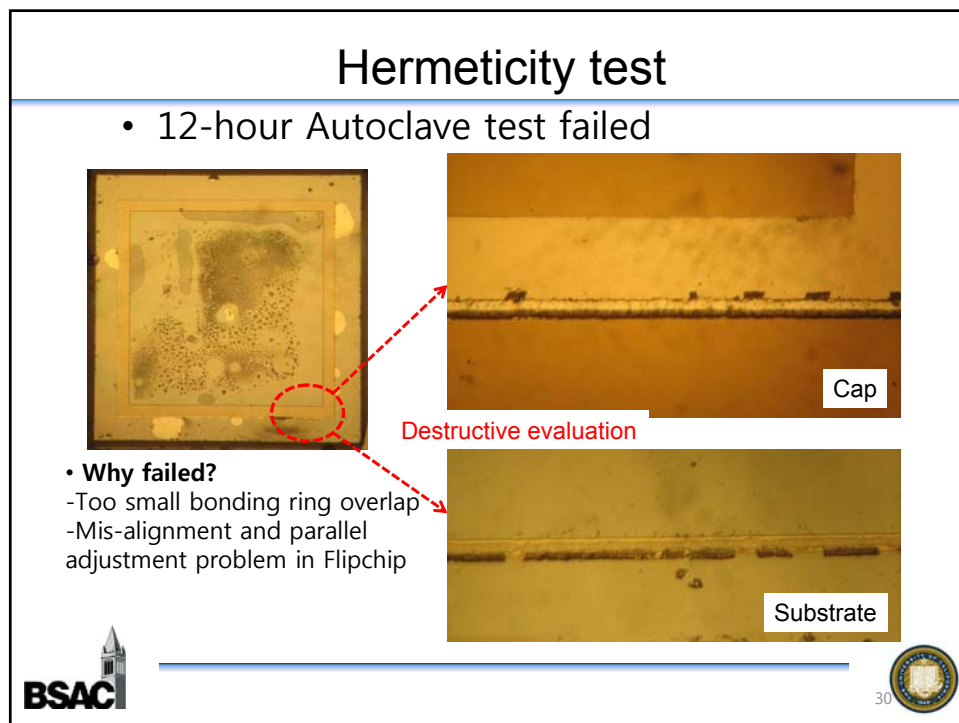
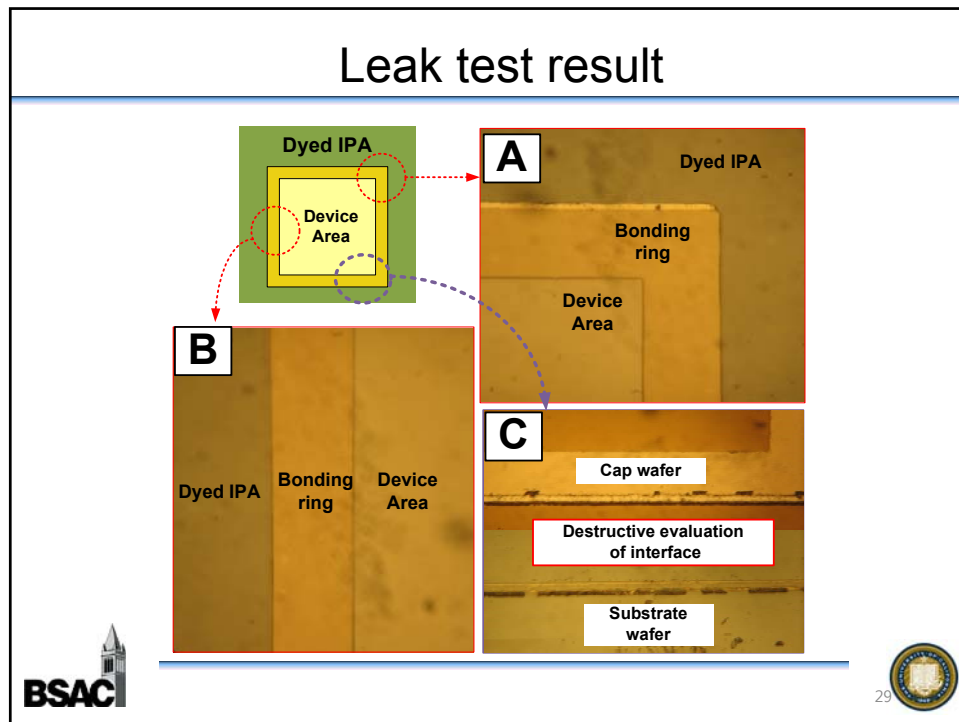


SnAg 10 μ m width ring pre-reflow optimization



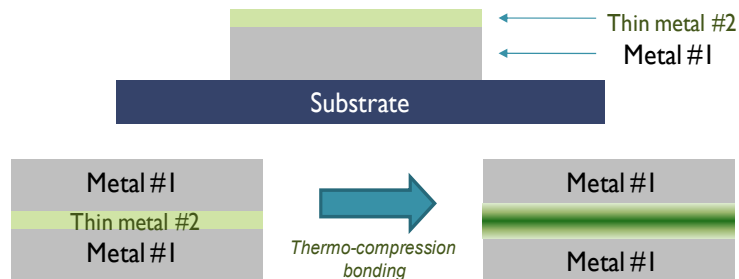




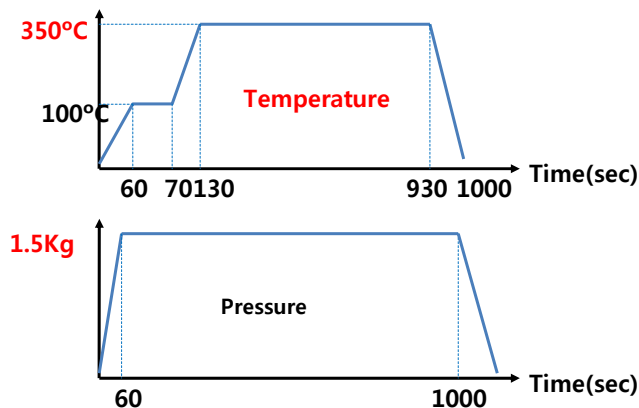


Thin metal layer insertion approach

- Alloy formation b/w bonding metal (Al)
- Stronger bonding than pure Al-Al bonding at same bonding condition



Temperature/pressure condition

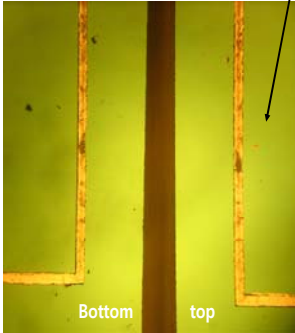


- Lower bonding pressure (15MPa)
- Lower bonding temperature (350°C, $T_m(\text{Al})=660^\circ\text{C}$)



Pull Test results


Adhesion layer on wafer (same color)



Width : 50 μ m

Bottom top



< Al to Al bonding >



Bottom top



<Al+Sn20nm to Al bonding>

- Same bonding parameter was applied for both cases
- Strong bonding at the contact interface for <Al+Sn20nm to Al bonding>
- No strong bond was made for Al to Al bonding case




Summary

- Proof-of-Concept : Metal bonding for possible replacement of glass-frit
 - CMOS-integrated process
 - Compatible mechanical strength with glass-frit
- Rapid Thermal bonding result(no pre-reflow)
 - Successful leak-test for 200 μ m bonding ring
 - Failed 12hr hermetic test
- Solder reflow profile optimization for sub-100 μ m metal bonding solution
 - Reflow profile optimization for 10mm SnAg bonding ring
 - Uniform half-cylinder shape reflow results
- Solder pre-reflow bonding of SnAg 10 μ m bonding ring using Flipchip
 - Optimized reflow profile used for bonding
 - Possibility of sub-100 μ m bonding ring in MEMS packaging
- Metal insertion approach
 - Al-Sn-Al approach showed better bonding quality than pure Al-Al bonding
 - Lower temperature and pressure



Acknowledgement

- IEEE-CPMT 
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- Mr. Kedar Shah
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 - Freescale™ semiconductor 
 - DARPA 

Thank you!!

